Document Title

256Kx16 bit Dynamic RAM with Fast Page Mode

Revision History

Revision No	History	Draft Date	Remark
0A	Initial Draft	August 11,2001	

256K x 16 (4-MBIT) DYNAMIC RAM WITH FAST PAGE MODE

FEATURES

- Fast access and cycle time
- TTL compatible inputs and outputs
- Refresh Interval: 512 cycles/8 ms
- Refresh Mode: $\overline{RAS}$-Only, $\overline{CAS}$-before-$\overline{RAS}$ (CBR), Hidden
- Self Refresh Mode: 512 cycles/64 ms (S version only)
- JEDEC standard pinout
- Single power supply:
  — 5V ± 10% (IC41C16257)
  — 3.3V ± 10% (IC41LV16257)
- Byte Write and Byte Read operation via two $\overline{CAS}$
- Available in 40-pin SOJ and TSOP-2

DESCRIPTION

The *ICSI* IC41C16257 and the IC41LV16257 are 262,144 x 16-bit high-performance CMOS Dynamic Random Access Memory. Fast Page Mode allows 512 random accesses within a single row with access cycle time as short as 12 ns per 16-bit word. The Byte Write control, of upper and lower byte, makes these devices ideal for use in 16-, 32-bit wide data bus systems.

These features make the IC41C16257 and the IC41LV16257 ideally suited for high band-width graphics, digital signal processing, high-performance computing systems, and peripheral applications.

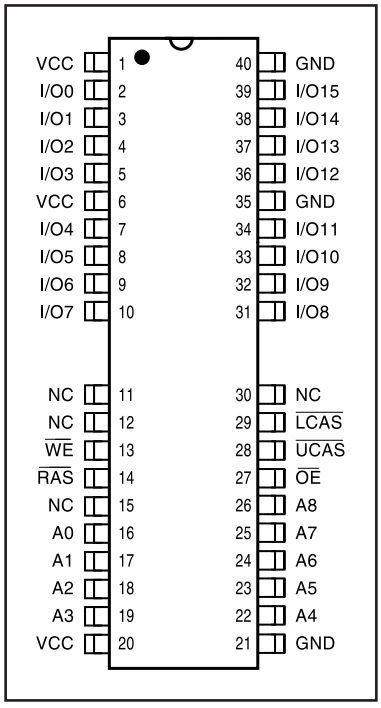
The IC41C16257 and the IC41LV16257 are packaged in a 40-pin, 400mil SOJ and TSOP-2.

KEY TIMING PARAMETERS

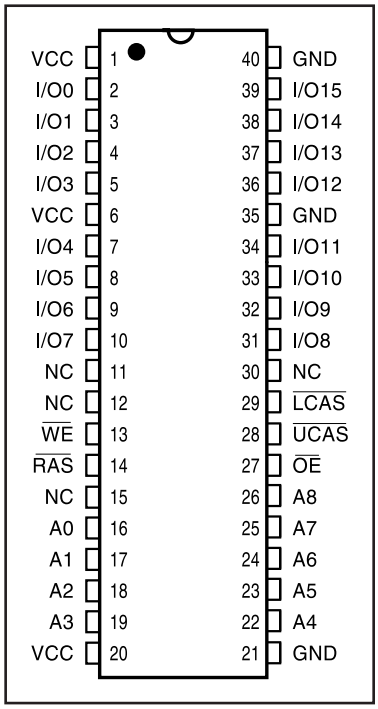
Parameter	-35	-50	-60	Unit
Max. $\overline{RAS}$ Access Time (t_{RAC})	35	50	60	ns
Max. $\overline{CAS}$ Access Time (t_{CAC})	10	14	15	ns
Max. Column Address Access Time (t_{AA})	18	25	30	ns
Min. Fast Page Mode Cycle Time (t_{PC})	12	20	25	ns
Min. Read/Write Cycle Time (t_{RC})	60	90	110	ns

PIN CONFIGURATIONS

40-Pin TSOP-2



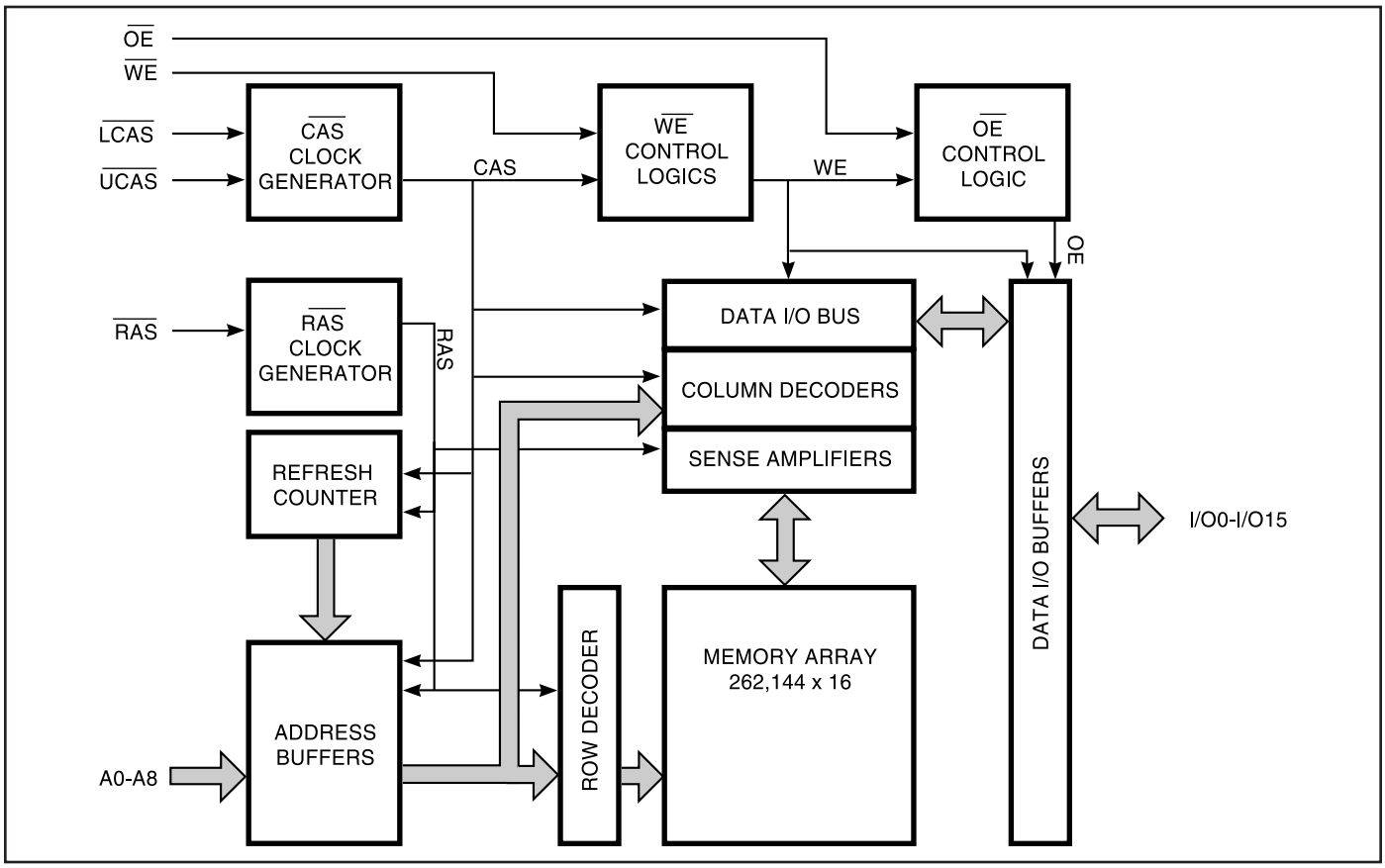
40-Pin SOJ



PIN DESCRIPTIONS

A0-A8	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
$\overline{WE}$	Write Enable
$\overline{OE}$	Output Enable
$\overline{RAS}$	Row Address Strobe
UCAS	Upper Column Address Strobe
$\overline{LCAS}$	Lower Column Address Strobe
Vcc	Power
GND	Ground
NC	No Connection

FUNCTIONAL BLOCK DIAGRAM



TRUTH TABLE

Function	$\overline{RAS}$	$\overline{LCAS}$	$\overline{UCAS}$	$\overline{WE}$	$\overline{OE}$	Address tR/tC	I/O
Standby	H	H	H	X	X	X	High-Z
Read: Word	L	L	L	H	L	ROW/COL	DOUT
Read: Lower Byte	L	L	H	H	L	ROW/COL	Lower Byte, DOUT Upper Byte, High-Z
Read: Upper Byte	L	H	L	H	L	ROW/COL	Lower Byte, High-Z Upper Byte, DOUT
Write: Word (Early Write)	L	L	L	L	X	ROW/COL	DIN
Write: Lower Byte (Early Write)	L	L	H	L	X	ROW/COL	Lower Byte, DIN Upper Byte, High-Z
Write: Upper Byte (Early Write)	L	H	L	L	X	ROW/COL	Lower Byte, High-Z Upper Byte, DIN
Read-Write(1,2)	L	L	L	H→L	L→H	ROW/COL	DOUT, DIN
Hidden Refresh2) Read	L→H→L	L	L	H	L	ROW/COL	DOUT
Write	L→H→L	L	L	L	X	ROW/COL	DOUT
$\overline{RAS}$-Only Refresh	L	H	H	X	X	ROW/NA	High-Z
CBR Refresh(3)	H→L	L	L	X	X	X	High-Z

Notes:
1. These WRITE cycles may also be BYTE WRITE cycles (either $\overline{LCAS}$ or $\overline{UCAS}$ active).
2. These READ cycles may also be BYTE READ cycles (either $\overline{LCAS}$ or $\overline{UCAS}$ active).
3. At least one of the two CAS signals must be active ($\overline{LCAS}$ or $\overline{UCAS}$).

FUNCTIONAL DESCRIPTION

The IC41C16257 and the IC41LV16257 are CMOS DRAMs optimized for high-speed bandwidth, low-power applications. During READ or WRITE cycles, each bit is uniquely addressed through the 18 address bits. These are entered nine bits (A0-A8) at a time. The row address is latched by the Row Address Strobe ($\overline{RAS}$). The column address is latched by the Column Address Strobe ($\overline{CAS}$). $\overline{RAS}$ is used to latch the first nine bits and $\overline{CAS}$ is used to latch the latter nine bits.

The IC41C16257 and the IC41LV16257 have two $\overline{CAS}$ controls, $\overline{LCAS}$ and $\overline{UCAS}$. The $\overline{LCAS}$ and $\overline{UCAS}$ inputs internally generate a $\overline{CAS}$ signal functioning in an identical manner to the single $\overline{CAS}$ input on the other 256K x 16 DRAMs. The key difference is that each $\overline{CAS}$ controls its corresponding I/O tristate logic (in conjunction with $\overline{OE}$ and $\overline{WE}$ and $\overline{RAS}$). $\overline{LCAS}$ controls I/O0 - I/O7 and $\overline{UCAS}$ controls I/O8 - I/O15.

The IC41C16257/IC41LV16257 $\overline{CAS}$ function is determined by the first $\overline{CAS}$ ($\overline{LCAS}$ or $\overline{UCAS}$) transitioning LOW and the last transitioning back HIGH. The two $\overline{CAS}$ controls give the IC41C16257 both BYTE READ and BYTE WRITE cycle capabilities.

Memory Cycle

A memory cycle is initiated by bringing $\overline{RAS}$ LOW and it is terminated by returning both $\overline{RAS}$ and $\overline{CAS}$ HIGH. To ensure proper device operation and data integrity any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. A new cycle must not be initiated until the minimum precharge time t_{RP}, t_{CP} has elapsed.

Read Cycle

A read cycle is initiated by the falling edge of $\overline{CAS}$ or $\overline{OE}$, whichever occurs last, while holding $\overline{WE}$ HIGH. The column address must be held for a minimum time specified by t_{AR}. Data Out becomes valid only when t_{RAC}, t_{AA}, t_{CAC} and t_{OE} are all satisfied. As a result, the access time is dependent on the timing relationships between these parameters.

Write Cycle

A write cycle is initiated by the falling edge of $\overline{CAS}$ and $\overline{WE}$, whichever occurs last. The input data must be valid at or before the falling edge of $\overline{CAS}$ or $\overline{WE}$, whichever occurs last.

Refresh Cycle

To retain data, 512 refresh cycles are required in each 8 ms period. There are two ways to refresh the memory:

1. By clocking each of the 512 row addresses (A0 through A8) with $\overline{RAS}$ at least once every 8 ms. Any read, write, read-modify-write or $\overline{RAS}$-only cycle refreshes the addressed row.
2. Using a $\overline{CAS}$-before-$\overline{RAS}$ refresh cycle. $\overline{CAS}$-before-$\overline{RAS}$ refresh is activated by the falling edge of $\overline{RAS}$, while holding $\overline{CAS}$ LOW. In $\overline{CAS}$-before-$\overline{RAS}$ refresh cycle, an internal 9-bit counter provides the row addresses and the external address inputs are ignored.

$\overline{CAS}$-before-$\overline{RAS}$ is a refresh-only mode and no data access or device selection is allowed. Thus, the output remains in the High-Z state during the cycle.

Self Refresh Cycle(1)

The Self Refresh allows the user a dynamic refresh, data retention mode at the extended refresh period of 64 ms. i.e., 125 µs per row when using distributed CBR refreshes. The feature also allows the user the choice of a fully static, low power data retention mode. The optional Self Refresh feature is initiated by performing a CBR Refresh cycle and holding $\overline{RAS}$ LOW for the specified t_{RASS}.

The Self Refresh mode is terminated by driving $\overline{RAS}$ HIGH for a minimum time of t_{RPS}. This delay allows for the completion of any internal refresh cycles that may be in process at the time of the $\overline{RAS}$ LOW-to-HIGH transition. If the DRAM controller uses a distributed refresh sequence, a burst refresh is not required upon exiting Self Refresh.

However, if the DRAM controller utilizes a $\overline{RAS}$-only or burst refresh sequence, all 512 rows must be refreshed within the average internal refresh rate, prior to the resumption of normal operation.

Power-On

After application of the V_{CC} supply, an initial pause of 200 µs is required followed by a minimum of eight initialization cycles (any combination of cycles containing a $\overline{RAS}$ signal).

During power-on, it is recommended that $\overline{RAS}$ track with V_{CC} or be held at a valid V_{IH} to avoid current surges.

Note:

1.Self Refresh is for Sversion only.

DR021-0A 08/11/2001

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameters		Rating	Unit
V_T	Voltage on Any Pin Relative to GND	5V	–1.0 to +7.0	V
		3.3V	–0.5 to +4.6	V
V_{CC}	Supply Voltage	5V	–1.0 to +7.0	V
		3.3V	–0.5 to +4.6	V
I_{OUT}	Output Current		50	mA
P_D	Power DICSIpation		1	W
T_A	Operation Temperature	Com.	0 to +70	°C
		Ind.	-40 to +85	°C
T_{STG}	Storage Temperature		–55 to +125	°C

Note:
1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING CONDITIONS (Voltages are referenced to GND)

Symbol	Parameter		Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	5V	4.5	5.0	5.5	V
		3.3V	3.0	3.3	3.6	V
V_{IH}	Input High Voltage	5V	2.4	—	V_{CC} + 1.0	V
		3.3V	2.0	—	V_{CC} + 0.3	V
V_{IL}	Input Low Voltage	5V	–1.0	—	0.8	V
		3.3V	–0.3	—	0.8	V
T_A	Ambient Temperature	Com.	0	—	70	°C
		Ind.	–40	—	85	°C

CAPACITANCE(1,2)

Symbol	Parameter	Max.	Unit
C_{IN1}	Input Capacitance: A0-A8	5	pF
C_{IN2}	Input Capacitance: $\overline{RAS}$, $\overline{UCAS}$, $\overline{LCAS}$, $\overline{WE}$, $\overline{OE}$	7	pF
C_{IO}	Data Input/Output Capacitance: I/O0-I/O15	7	pF

Notes:
1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V + 10%, or V_{CC} = 3.3V + 10%.

ELECTRICAL CHARACTERISTICS[1] (Recommended Operation Conditions unless otherwise noted.)

Symbol	Parameter	Test Condition		Speed	Min.	Max.	Unit
I_{IL}	Input Leakage Current	Any input 0V ≤ V_{IN} ≤ Vcc Other inputs not under test = 0V			–10	10	µA
I_{IO}	Output Leakage Current	Output is disabled (Hi-Z) 0V ≤ V_{OUT} ≤ Vcc			–10	10	µA
V_{OH}	Output High Voltage Level	I_{OH} = –2.5 mA			2.4	—	V
V_{OL}	Output Low Voltage Level	I_{OL} = +2.1 mA			—	0.4	V
I_{CC1}	Stand-by Current: TTL	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$ ≥ V_{IH}	Com.	5V	—	2	mA
			Ind.	5V	—	3	mA
I_{CC1}	Stand-by Current: TTL	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$ ≥ V_{IH}	Com.	3.3V	—	1	mA
			Ind.	3.3V	—	2	mA
I_{CC2}	Stand-by Current: CMOS	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$ ≥ V_{CC} – 0.2V		5V	—	1	mA
I_{CC2}	Stand-by Current: CMOS	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$ ≥ V_{CC} – 0.2V		3.3V	—	0.5	mA
I_{CC3}	Operating Current: Random Read/Write[2,3,4] Average Power Supply Current	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$, Address Cycling, t_{RC} = t_{RC} (min.)		-35 -50 -60	— — —	230 180 170	mA
I_{CC4}	Operating Current: Fast Page Mode[2,3,4] Average Power Supply Current	$\overline{RAS}$ = V_{IL}, $\overline{LCAS}$, $\overline{UCAS}$, Cycling t_{PC} = t_{PC} (min.)		-35 -50 -60	— — —	220 170 160	mA
I_{CC5}	Refresh Current: $\overline{RAS}$-Only[2,3] Average Power Supply Current	$\overline{RAS}$ Cycling, $\overline{LCAS}$, $\overline{UCAS}$ ≥ V_{IH} t_{RC} = t_{RC} (min.)		-35 -50 -60	— — —	230 180 170	mA
I_{CC6}	Refresh Current: CBR[2,3,5] Average Power Supply Current	$\overline{RAS}$, $\overline{LCAS}$, $\overline{UCAS}$ Cycling t_{RC} = t_{RC} (min.)		-35 -50 -60	— — —	230 180 170	mA
I_{CCS}	Self Refresh current[6]	Self Refresh Mode		5V	—	300	µA
				3.3V	—	300	µA

Notes:
1. An initial pause of 200 µs is required after power-up followed by eight $\overline{RAS}$ refresh cycles ($\overline{RAS}$-Only or CBR) before proper device operation is assured.The eight $\overline{RAS}$ cycles wake-up should be repeated any time the t_{REF} refresh requirement is exceeded.
2. Dependent on cycle rates.
3. Specified values are obtained with minimum cycle time and the output open.
4. Column-address is changed once each fast page cycle.
5. Enables on-chip refresh and address counters.
6. I_{CCS} is for S version only.

AC CHARACTERISTICS[1,2,3,4,5,6]

(Recommended Operating Conditions unless otherwise noted.)

Symbol	Parameter	-35 Min.	-35 Max.	-50 Min.	-50 Max.	-60 Min.	-60 Max.	Units
t_{RC}	Random READ or WRITE Cycle Time	60	—	90	—	110	—	ns
t_{RAC}	Access Time from $\overline{RAS}$[6, 7]	—	35	—	50	—	60	ns
t_{CAC}	Access Time from $\overline{CAS}$[6, 8, 15]	—	10	—	14	—	15	ns
t_{AA}	Access Time from Column-Address[6]	—	18	—	25	—	30	ns
t_{RAS}	$\overline{RAS}$ Pulse Width	35	10K	50	10K	60	10K	ns
t_{RP}	$\overline{RAS}$ Precharge Time	20	—	30	—	40	—	ns
t_{CAS}	$\overline{CAS}$ Pulse Width[26]	6	10K	8	10K	10	10K	ns
t_{CP}	$\overline{CAS}$ Precharge Time[9, 25]	5	—	8	—	10	—	ns
t_{CSH}	$\overline{CAS}$ Hold Time [21]	35	—	50	—	60	—	ns
t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay Time[10, 20]	11	28	19	36	20	45	ns
t_{ASR}	Row-Address Setup Time	0	—	0	—	0	—	ns
t_{RAH}	Row-Address Hold Time	6	—	8	—	10	—	ns
t_{ASC}	Column-Address Setup Time[20]	0	—	0	—	0	—	ns
t_{CAH}	Column-Address Hold Time[20]	6	—	8	—	10	—	ns
t_{AR}	Column-Address Hold Time (referenced to $\overline{RAS}$)	30	—	40	—	40	—	ns
t_{RAD}	$\overline{RAS}$ to Column-Address Delay Time[11]	12	20	14	25	15	30	ns
t_{RAL}	Column-Address to $\overline{RAS}$ Lead Time	18	—	25	—	30	—	ns
t_{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	0	—	0	—	0	—	ns
t_{RSH}	$\overline{RAS}$ Hold Time[27]	8	—	14	—	15	—	ns
t_{CLZ}	$\overline{CAS}$ to Output in Low-Z[15, 29]	3	—	3	—	3	—	ns
t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time[21]	5	—	5	—	5	—	ns
t_{OD}	Output Disable Time[19, 28, 29]	3	15	3	15	3	15	ns
t_{OE}	Output Enable Time[15, 16]	—	10	—	15	—	15	ns
t_{OES}	$\overline{OE}$ LOW to $\overline{CAS}$ HIGH Setup Time	5	—	5	—	5	—	ns
t_{RCS}	Read Command Setup Time[17, 20]	0	—	0	—	0	—	ns
t_{RRH}	Read Command Hold Time (referenced to $\overline{RAS}$)[12]	0	—	0	—	0	—	ns
t_{RCH}	Read Command Hold Time (referenced to $\overline{CAS}$)[12, 17, 21]	0	—	0	—	0	—	ns
t_{WCH}	Write Command Hold Time[17, 27]	5	—	8	—	10	—	ns
t_{WCR}	Write Command Hold Time (referenced to $\overline{RAS}$)[17]	30	—	40	—	50	—	ns
t_{WP}	Write Command Pulse Width[17]	5	—	8	—	10	—	ns
t_{RWL}	Write Command to $\overline{RAS}$ Lead Time[17]	8	—	14	—	15	—	ns
t_{CWL}	Write Command to $\overline{CAS}$ Lead Time[17, 21]	8	—	14	—	15	—	ns
t_{WCS}	Write Command Setup Time[14, 17, 20]	0	—	0	—	0	—	ns
t_{DHR}	Data-in Hold Time (referenced to $\overline{RAS}$)	30	—	40	—	45	—	ns

(Continued)

AC CHARACTERISTICS(1,2,3,4,5,6)

(Recommended Operating Conditions unless otherwise noted.)

Symbol	Parameter	-35 Min.	-35 Max.	-50 Min.	-50 Max.	-60 Min.	-60 Max.	Units
t_{ACH}	Column-Address Setup Time to $\overline{CAS}$ Precharge during WRITE Cycle	15	—	15	—	15	—	ns
t_{OEH}	$\overline{OE}$ Hold Time from $\overline{WE}$ during READ-MODIFY-WRITE cycle(18)	8	—	10	—	15	—	ns
t_{DS}	Data-In Setup Time(15, 22)	0	—	0	—	0	—	ns
t_{DH}	Data-In Hold Time(15, 22)	6	—	8	—	10	—	ns
t_{RWC}	READ-MODIFY-WRITE Cycle Time	80	—	125	—	140	—	ns
t_{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay Time during READ-MODIFY-WRITE Cycle(14)	45	—	70	—	80	—	ns
t_{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay Time(14, 20)	25	—	34	—	36	—	ns
t_{AWD}	Column-Address to $\overline{WE}$ Delay Time(14)	30	—	42	—	49	—	ns
t_{PC}	Fast Page Mode READ or WRITE Cycle Time(24)	12	—	20	—	25	—	ns
t_{RASP}	Fast Page Mode $\overline{RAS}$ Pulse Width	35	100K	50	100K	60	100K	ns
t_{CPA}	Access Time from $\overline{CAS}$ Precharge(15)	—	21	—	27	—	34	ns
t_{PRWC}	Fast Page Mode READ-WRITE Cycle Time(24)	40	—	47	—	56	—	ns
t_{OFF}	Output Buffer Turn-Off Delay from $\overline{CAS}$ or $\overline{RAS}$(13,15,19, 29)	3	15	3	15	3	15	ns
t_{CLCH}	Last $\overline{CAS}$ going LOW to First $\overline{CAS}$ returning HIGH(23)	10	—	10	—	10	—	ns
t_{CSR}	$\overline{CAS}$ Setup Time (CBR REFRESH)(30, 20)	8	—	10	—	10	—	ns
t_{CHR}	$\overline{CAS}$ Hold Time (CBR REFRESH)(30, 21)	8	—	10	—	10	—	ns
t_{ORD}	$\overline{OE}$ Setup Time prior to $\overline{RAS}$ during HIDDEN REFRESH Cycle	0	—	0	—	0	—	ns
t_{REF}	Refresh Period (512 Cycles)	—	8	—	8	—	8	ms
t_T	Transition Time (Rise or Fall)(2, 3)	1	50	1	50	1	50	ns

AC TEST CONDITIONS

Output load: Two TTL Loads and 50 pF (Vcc = 5.0V ±10%)
One TTL Load and 50 pF (Vcc = 3.3V ±10%)

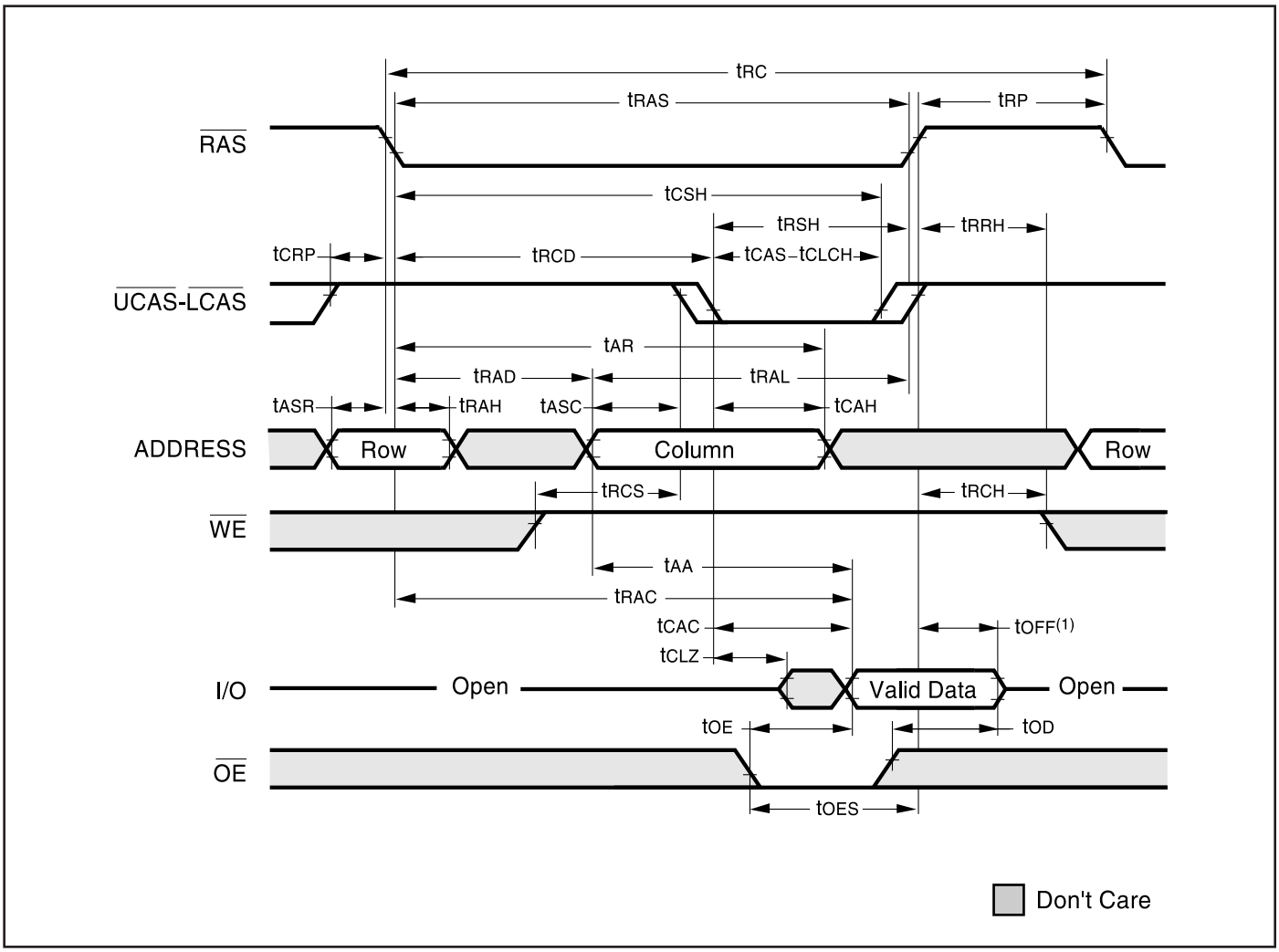
Input timing reference levels: V_{IH} = 2.4V, V_{IL} = 0.8V (Vcc = 5.0V ±10%);
V_{IH} = 2.0V, V_{IL} = 0.8V (Vcc = 3.3V ±10%)

Output timing reference levels: V_{OH} = 2.0V, V_{OL} = 0.8V (Vcc = 5V ±10%, 3.3V ±10%)

Notes:

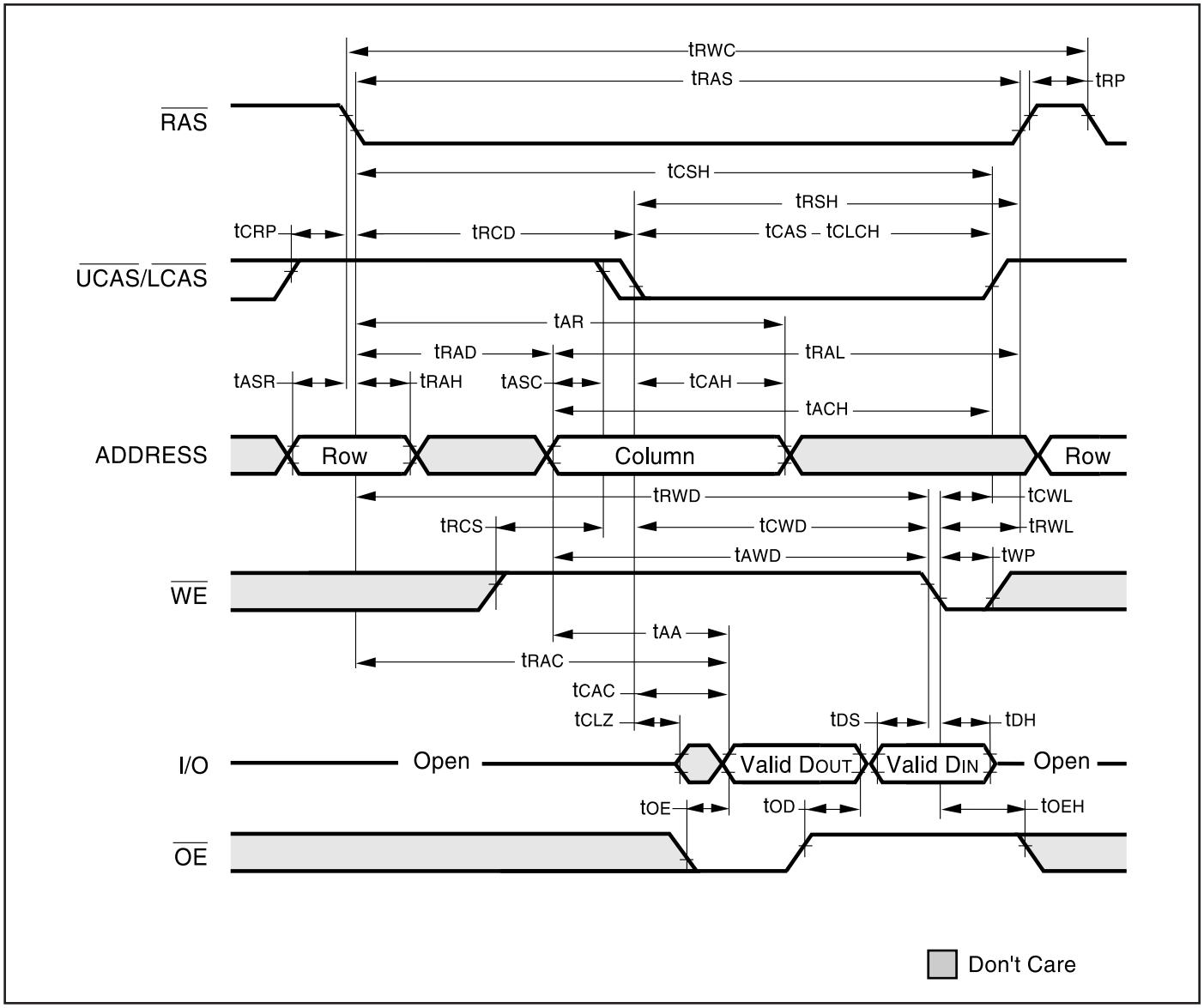
1. An initial pause of 200 µs is required after power-up followed by eight $\overline{RAS}$ refresh cycle ($\overline{RAS}$-Only or CBR) before proper device operation is assured. The eight $\overline{RAS}$ cycles wake-up should be repeated any time the t_{REF} refresh requirement is exceeded.
2. V_{IH} (MIN) and V_{IL} (MAX) are reference levels for measuring timing of input signals. Transition times, are measured between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) and assume to be 1 ns for all inputs.
3. In addition to meeting the transition rate specification, all input signals must transit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
4. If $\overline{CAS}$ and $\overline{RAS}$ = V_{IH}, data output is High-Z.
5. If $\overline{CAS}$ = V_{IL}, data output may contain data from the last valid READ cycle.
6. Measured with a load equivalent to one TTL gate and 50 pF.
7. Assumes that $t_{RCD} \leq t_{RCD}$ (MAX). If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will increase by the amount that t_{RCD} exceeds the value shown.
8. Assumes that $t_{RCD} \geq t_{RCD}$ (MAX).
9. If $\overline{CAS}$ is LOW at the falling edge of $\overline{RAS}$, data out will be maintained from the previous cycle. To initiate a new cycle and clear the data output buffer, $\overline{CAS}$ and $\overline{RAS}$ must be pulsed for t_{CP}.
10. Operation with the t_{RCD} (MAX) limit ensures that t_{RAC} (MAX) can be met. t_{RCD} (MAX) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (MAX) limit, access time is controlled exclusively by t_{CAC}.
11. Operation within the t_{RAD} (MAX) limit ensures that t_{RCD} (MAX) can be met. t_{RAD} (MAX) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (MAX) limit, access time is controlled exclusively by t_{AA}.
12. Either t_{RCH} or t_{RRH} must be satisfied for a READ cycle.
13. t_{OFF} (MAX) defines the time at which the output achieves the open circuit condition; it is not a reference to V_{OH} or V_{OL}.
14. t_{WCS}, t_{RWD}, t_{AWD} and t_{CWD} are restrictive operating parameters in LATE WRITE and READ-MODIFY-WRITE cycle only. If $t_{WCS} \geq t_{WCS}$ (MIN), the cycle is an EARLY WRITE cycle and the data output will remain open circuit throughout the entire cycle. If $t_{RWD} \geq t_{RWD}$ (MIN), $t_{AWD} \geq t_{AWD}$ (MIN) and $t_{CWD} \geq t_{CWD}$ (MIN), the cycle is a READ-WRITE cycle and the data output will contain data read from the selected cell. If neither of the above conditions is met, the state of I/O (at access time and until $\overline{CAS}$ and $\overline{RAS}$ or $\overline{OE}$ go back to V_{IH}) is indeterminate. $\overline{OE}$ held HIGH and $\overline{WE}$ taken LOW after $\overline{CAS}$ goes LOW result in a LATE WRITE ($\overline{OE}$-controlled) cycle.
15. Output parameter (I/O) is referenced to corresponding $\overline{CAS}$ input, I/O0-I/O7 by $\overline{LCAS}$ and I/O8-I/O15 by $\overline{UCAS}$.
16. During a READ cycle, if $\overline{OE}$ is LOW then taken HIGH before $\overline{CAS}$ goes HIGH, I/O goes open. If $\overline{OE}$ is tied permanently LOW, a LATE WRITE or READ-MODIFY-WRITE is not possible.
17. Write command is defined as $\overline{WE}$ going low.
18. LATE WRITE and READ-MODIFY-WRITE cycles must have both t_{OD} and t_{OEH} met ($\overline{OE}$ HIGH during WRITE cycle) in order to ensure that the output buffers will be open during the WRITE cycle. The I/Os will provide the previously written data if $\overline{CAS}$ remains LOW and $\overline{OE}$ is taken back to LOW after t_{OEH} is met.
19. The I/Os are in open during READ cycles once t_{OD} or t_{OFF} occur.
20. The first $\chi\overline{CAS}$ edge to transition LOW.
21. The last $\chi\overline{CAS}$ edge to transition HIGH.
22. These parameters are referenced to $\overline{CAS}$ leading edge in EARLY WRITE cycles and $\overline{WE}$ leading edge in LATE WRITE or READ-MODIFY-WRITE cycles.
23. Last falling $\chi\overline{CAS}$ edge to first rising $\chi\overline{CAS}$ edge.
24. Last rising $\chi\overline{CAS}$ edge to next cycle's last rising $\chi\overline{CAS}$ edge.
25. Last rising $\chi\overline{CAS}$ edge to first falling $\chi\overline{CAS}$ edge.
26. Each $\chi\overline{CAS}$ must meet minimum pulse width.
27. Last $\chi\overline{CAS}$ to go LOW.
28. I/Os controlled, regardless $\overline{UCAS}$ and $\overline{LCAS}$.
29. The 3 ns minimum is a parameter guaranteed by design.
30. Enables on-chip refresh and address counters.

READ CYCLE

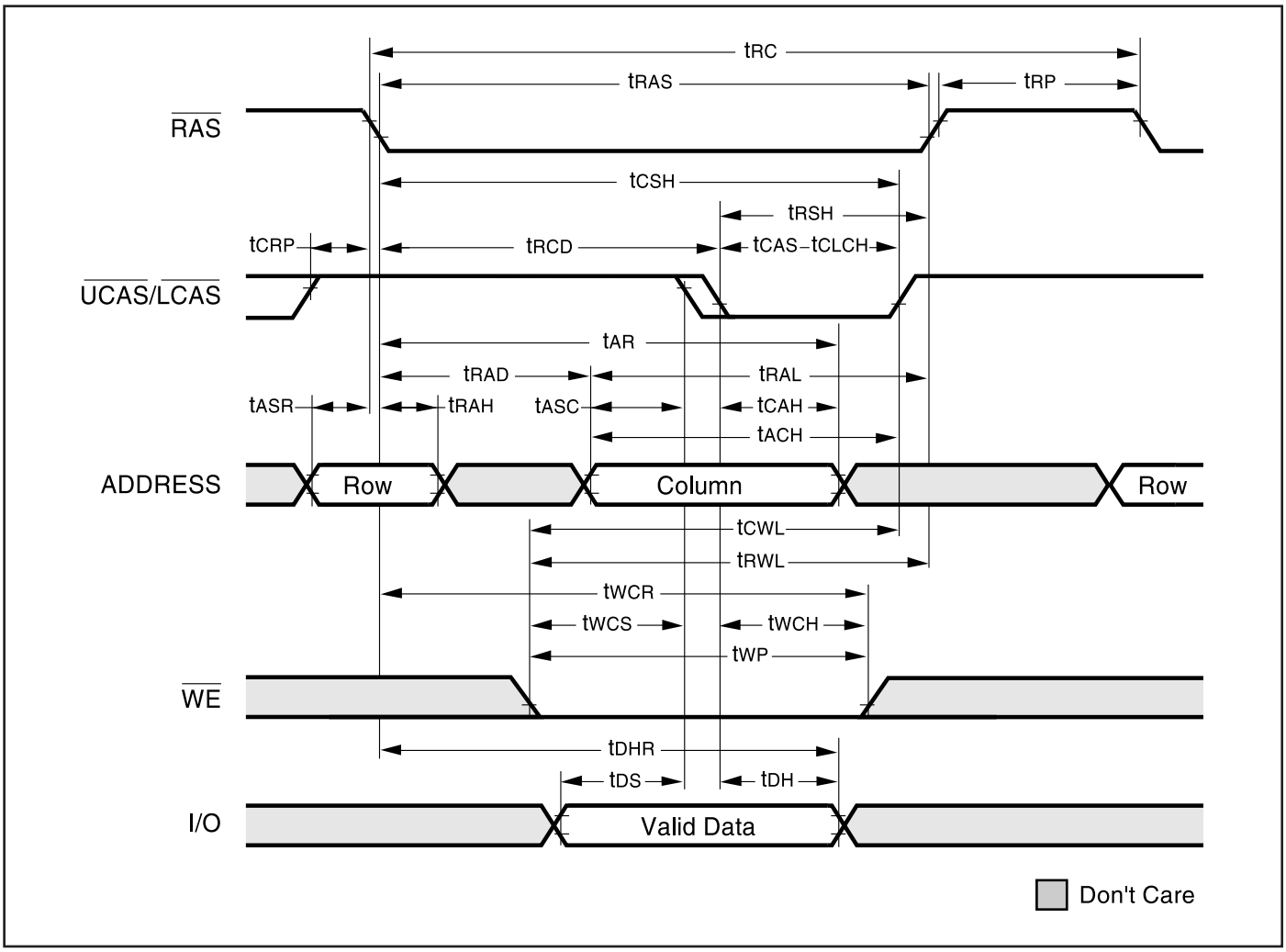


Note:
1. tOFF is referenced from rising edge of $\overline{RAS}$ or $\overline{CAS}$, whichever occurs last.

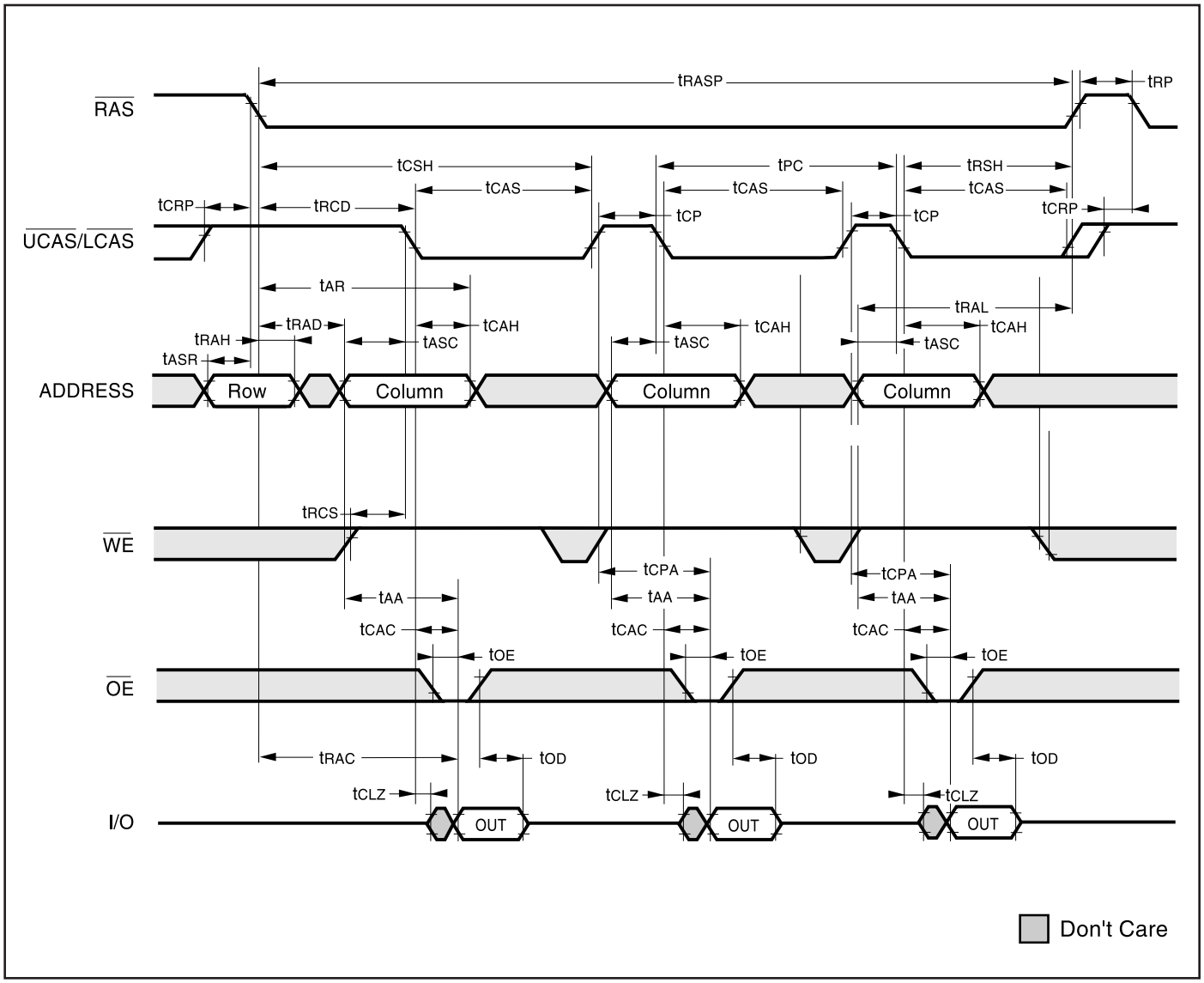
READ WRITE CYCLE (LATE WRITE and READ-MODIFY-WRITE Cycles)



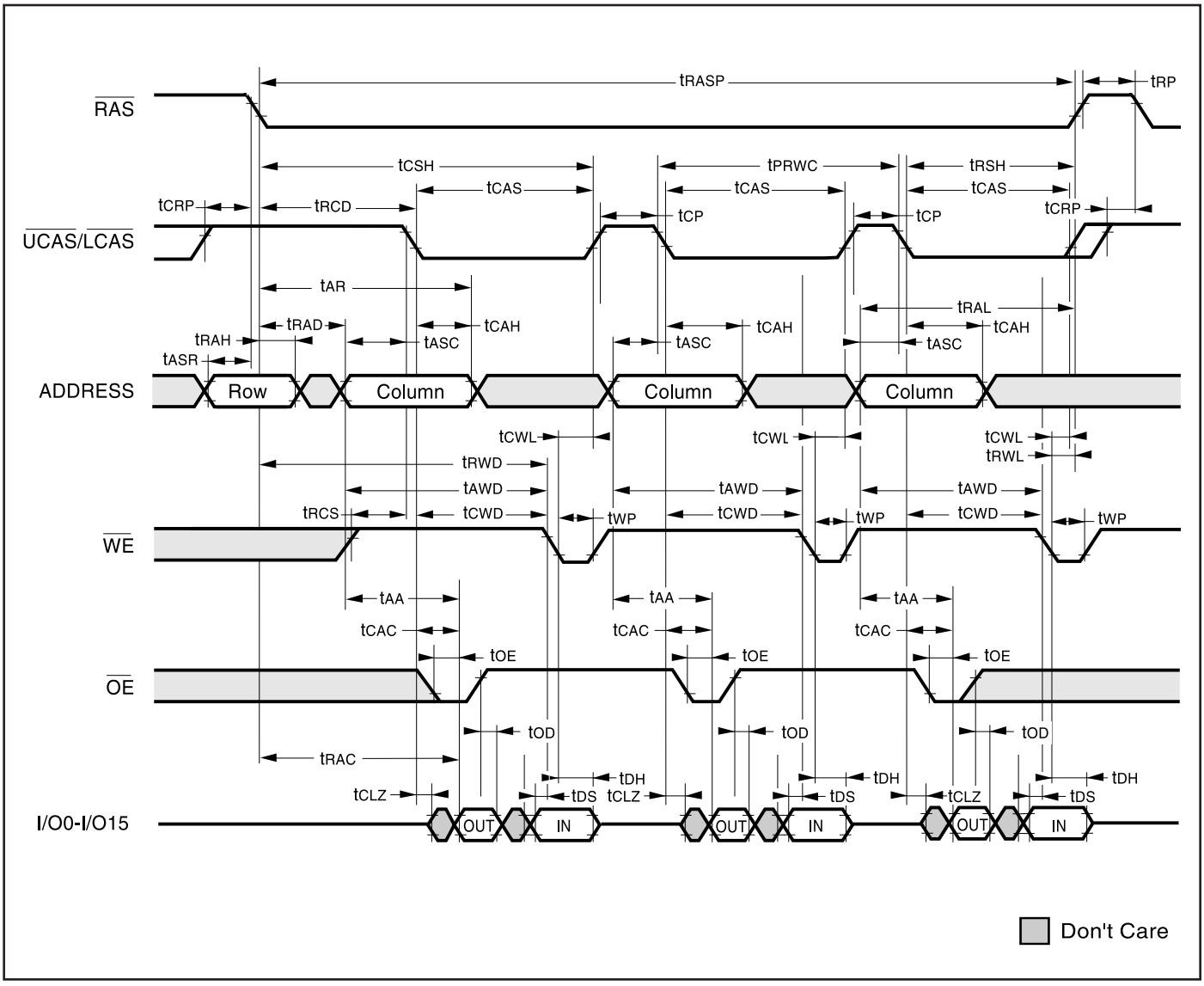
EARLY WRITE CYCLE ($\overline{OE}$ = DON'T CARE)



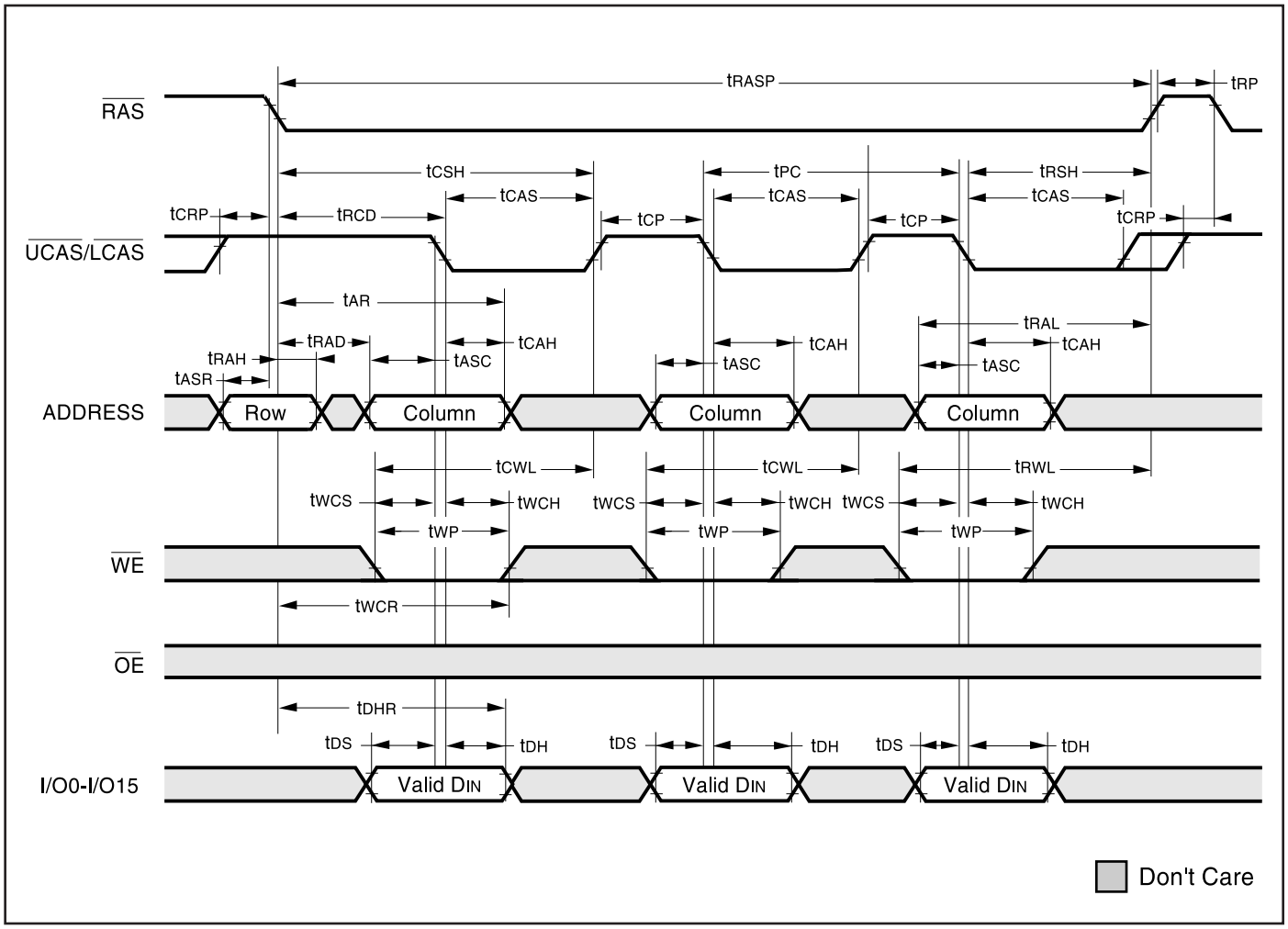
FAST PAGE MODE READ CYCLE



FAST PAGE MODE READ WRITE CYCLE (LATE WRITE and READ-MODIFY-WRITE Cycles)

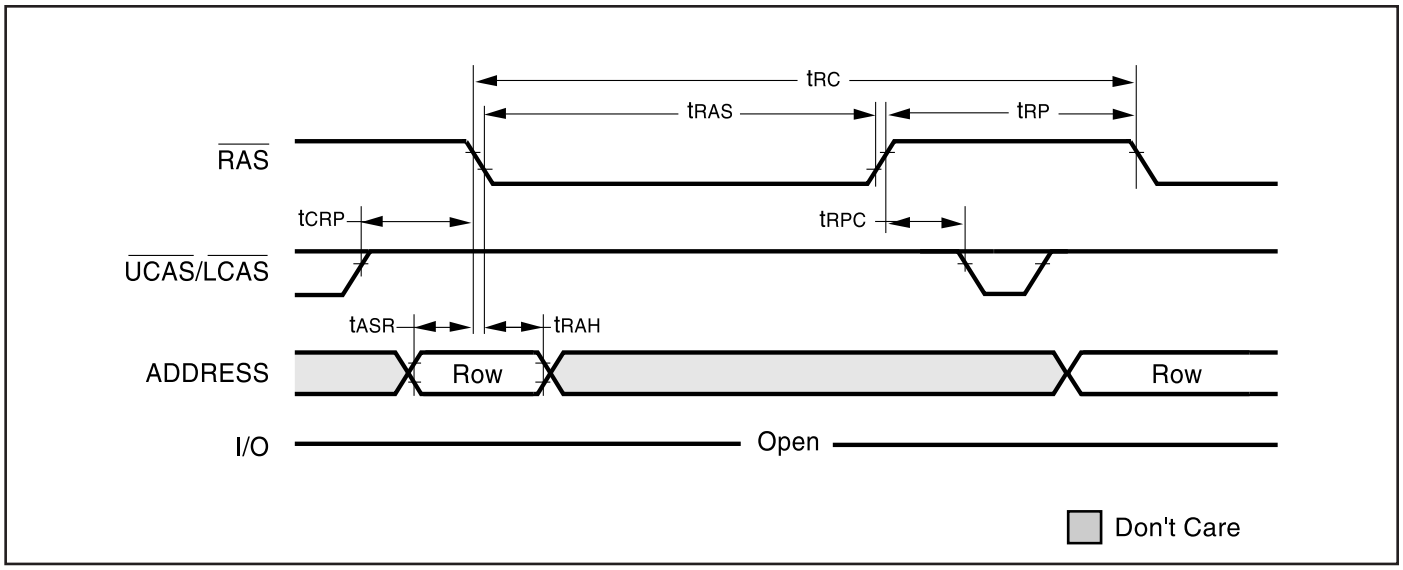


FAST PAGE MODE EARLY WRITE CYCLE

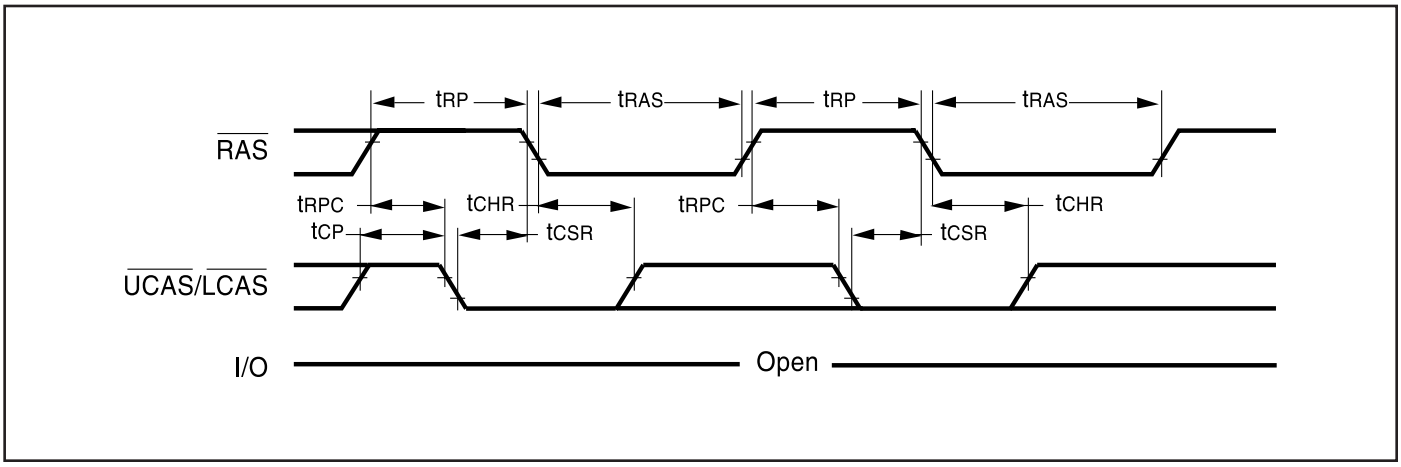


AC WAVEFORMS

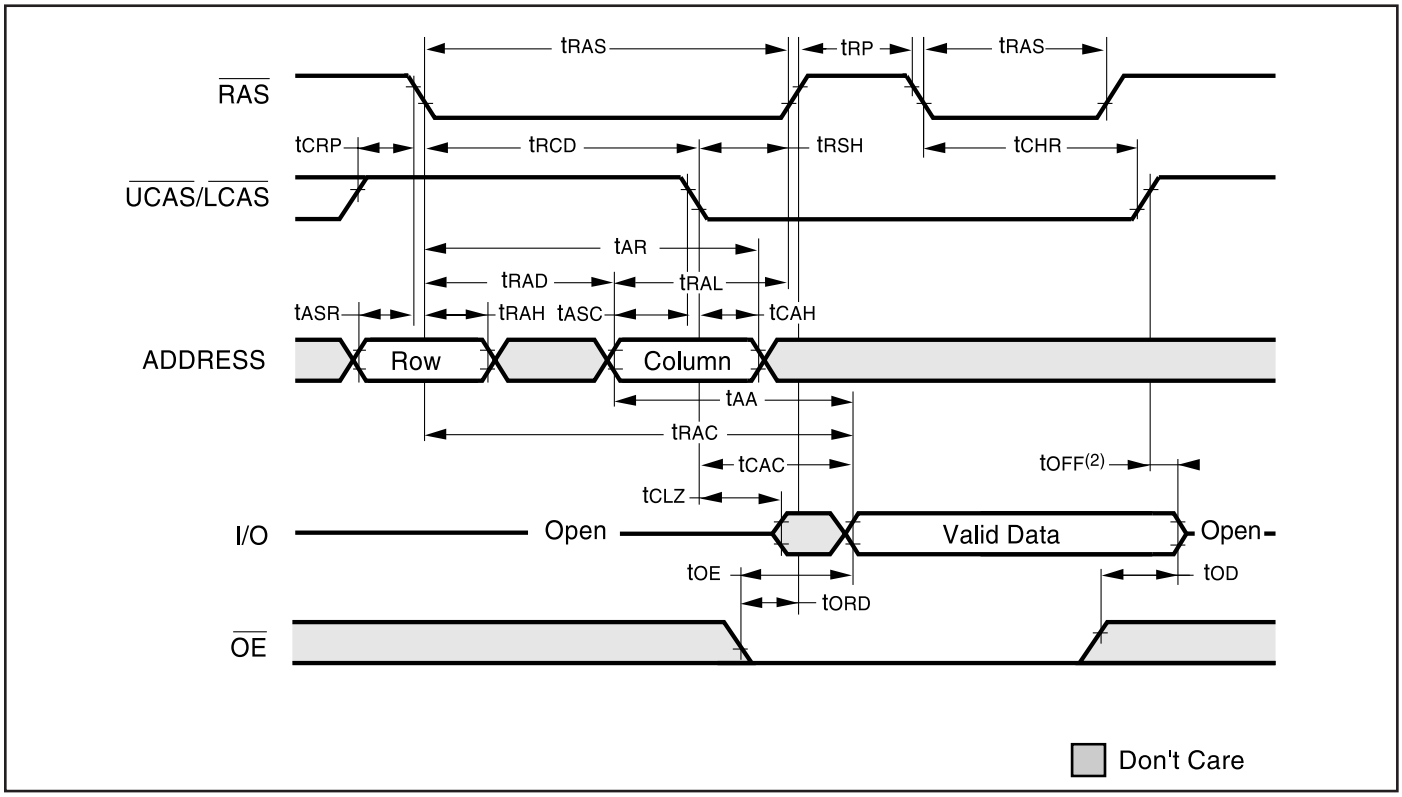
RAS-ONLY REFRESH CYCLE (OE, WE = DON'T CARE)



CBR REFRESH CYCLE (Addresses; $\overline{WE}$, $\overline{OE}$ = DON'T CARE)

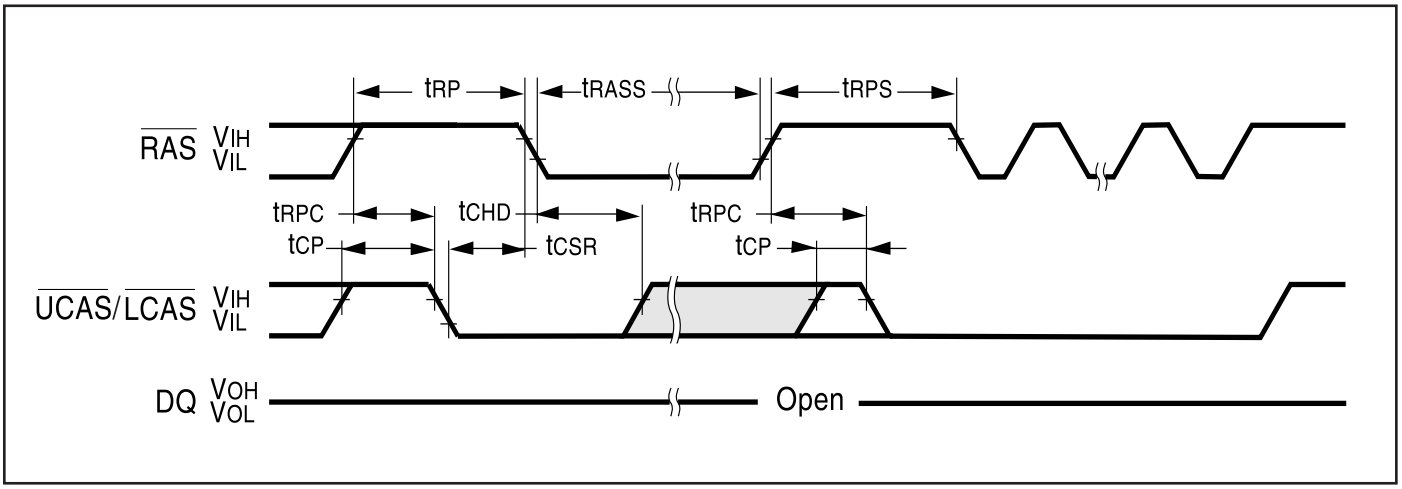


HIDDEN REFRESH CYCLE(1) ($\overline{WE}$ = HIGH; $\overline{OE}$ = LOW)



Notes:
1. A Hidden Refresh may also be performed after a Write Cycle. In this case, $\overline{WE}$ = LOW and $\overline{OE}$ = HIGH.
2. tOFF is referenced from rising edge of $\overline{RAS}$ or $\overline{CAS}$, whichever occurs last.

SELF REFRESH CYCLE (Addresses : $\overline{WE}$ and $\overline{OE}$ = DON'T CARE)



TIMING PARAMETERS

Symbol	-35 Min.	-35 Max.	-50 Min.	-50 Max.	-60 Min.	-60 Max.	Units
t_{CHD}	8	—	10	—	10	—	ns
t_{CP}	5	—	9	—	9	—	ns
t_{CSR}	8	—	10	—	10	—	ns
t_{RASS}	100	—	100	—	100	—	µs
t_{RP}	20	—	30	—	40	—	ns
t_{RPS}	64	—	84	—	104	—	ns
t_{RPC}	5	—	5	—	5	—	ns

ORDERING INFORMATION

IC41C16257

Commercial Range: 0°C to 70°C

Speed (ns)	Order Part No.	Package
35	IC41C16257-35K	400mil SOJ
	IC41C16257-35T	400mil TSOP-2
50	IC41C16257-50K	400mil SOJ
	IC41C16257-50T	400mil TSOP-2
60	IC41C16257-60K	400mil SOJ
	IC41C16257-60T	400mil TSOP-2

Industrial Range: -40°C to 85°C

Speed (ns)	Order Part No.	Package
35	IC41C16257-35KI	400mil SOJ
	IC41C16257-35TI	400mil TSOP-2
50	IC41C16257-50KI	400mil SOJ
	IC41C16257-50TI	400mil TSOP-2
60	IC41C16257-60KI	400mil SOJ
	IC41C16257-60TI	400mil TSOP-2

ORDERING INFORMATION

IC41LV16257

Commercial Range: 0°C to 70°C

Speed (ns)	Order Part No.	Package
35	IC41LV16257-35K	400mil SOJ
	IC41LV16257-35T	400mil TSOP-2
50	IC41LV16257-50K	400mil SOJ
	IC41LV16257-50T	400mil TSOP-2
60	IS41LV16257-60K	400mil SOJ
	IC41LV16257-60T	400mil TSOP-2

Industrial Range: -40°C to 85°C

Speed (ns)	Order Part No.	Package
35	IC41LV16257-35KI	400mil SOJ
	IC41LV16257-35TI	400mil TSOP-2
50	IC41LV16257-50KI	400mil SOJ
	IC41LV16257-50TI	400mil TSOP-2
60	IC41LV16257-60KI	400mil SOJ
	IC41LV16257-60TI	400mil TSOP-2

ORDERING INFORMATION

IC41C16257S

Commercial Range: 0°C to 70°C

Speed(ns)	OrderPartNo.	Package
35	IC41C16257S-35K	400mil SOJ
	IC41C16257S-35T	400mil TSOP-2
50	IC41C16257S-50K	400mil SOJ
	IC41C16257S-50T	400mil TSOP-2
60	IC41C16257S-60K	400mil SOJ
	IC41C16257S-60T	400mil TSOP-2

Industrial Range: -40°C to 85°C

Speed(ns)	Order PartNo.	Package
35	IC41C16257S-35KI	400mil SOJ
	IC41C16257S-35TI	400mil TSOP-2
50	IC41C16257S-50KI	400mil SOJ
	IC41C16257S-50TI	400mil TSOP-2
60	IC41C16257S-60KI	400mil SOJ
	IC41C16257S-60TI	400mil TSOP-2

ORDERING INFORMATION

IC41LV16257S

Commercial Range: 0°C to 70°C

Speed(ns)	OrderPartNo.	Package
35	IC41LV16257S-35K	400mil SOJ
	IC41LV16257S-35T	400mil TSOP-2
50	IC41LV16257S-50K	400mil SOJ
	IC41LV16257S-50T	400mil TSOP-2
60	IS41LV16257S-60K	400mil SOJ
	IC41LV16257S-60T	400mil TSOP-2

Industrial Range: -40°C to 85°C

Speed(ns)	OrderPartNo.	Package
35	IC41LV16257S-35KI	400mil SOJ
	IC41LV16257S-35TI	400mil TSOP-2
50	IC41LV16257S-50KI	400mil SOJ
	IC41LV16257S-50TI	400mil TSOP-2
60	IC41LV16257S-60KI	400mil SOJ
	IC41LV16257S-60TI	400mil TSOP-2

Integrated Circuit Solution Inc.
HEADQUARTER:
NO.2, TECHNOLOGY RD. V, SCIENCE-BASED INDUSTRIAL PARK,
HSIN-CHU, TAIWAN, R.O.C.
TEL: 886-3-5780333
Fax: 886-3-5783000

BRANCH OFFICE:
7F, NO. 106, SEC. 1, HSIN-TAI 5TH ROAD,
HSICHIH TAIPEI COUNTY, TAIWAN, R.O.C.
TEL: 886-2-26962140
FAX: 886-2-26962252
http://www.icsi.com.tw